

**Silicon NPN Power Transistors**

**2SC3970 2SC3970A**

**DESCRIPTION**

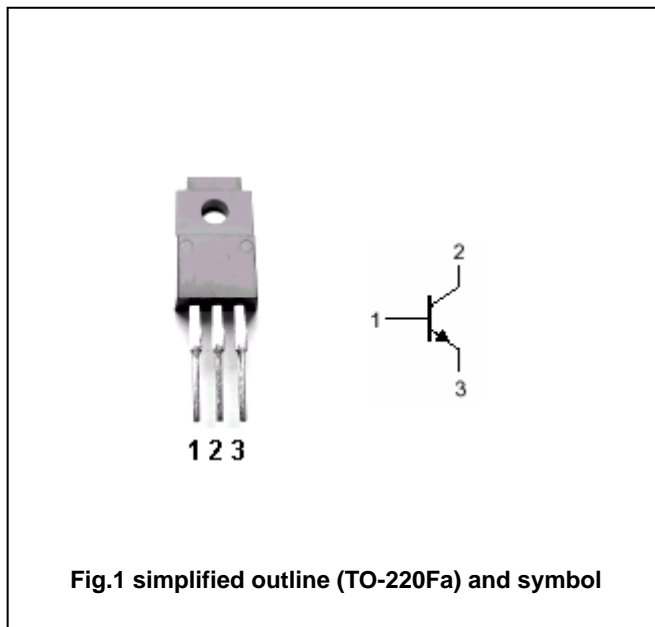
- With TO-220Fa package
- High speed switching
- High  $V_{CBO}$
- Wide area of safe operation

**APPLICATIONS**

- For high breakdown voltate ,high-speed switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2SC3970	800	V
		2SC3970A	900	
$V_{CEO}$	Collector-emitter voltage	Open base	500	V
$V_{EBO}$	Emitter-base voltage	Open collector	8	V
$I_C$	Collector current (DC)		1.5	A
$I_{CM}$	Collector current-Peak		3.0	A
$I_B$	Base current		0.5	A
$P_C$	Collector power dissipation	$T_c=25$	25	W
		$T_a=25$	2	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	500			V	
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.6A; I <sub>B</sub> =0.17A			1.0	V	
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =0.6A; I <sub>B</sub> =0.17A			1.5	V	
I <sub>CBO</sub>	Collector cut-off current	2SC3970	V <sub>CB</sub> =800V; I <sub>E</sub> =0			0.1	mA
		2SC3970A	V <sub>CB</sub> =900V; I <sub>E</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA	
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V	15				
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =0.6A; V <sub>CE</sub> =5V	8				
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A; V <sub>CE</sub> =10V; f=1MHz		20		MHz	

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =0.6A; I <sub>B1</sub> =0.17A I <sub>B2</sub> =-0.34A; V <sub>CC</sub> =200V			1.0	μs
t <sub>s</sub>	Storage time				3.0	μs
t <sub>f</sub>	Fall time				0.3	μs

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PACKAGE OUTLINE

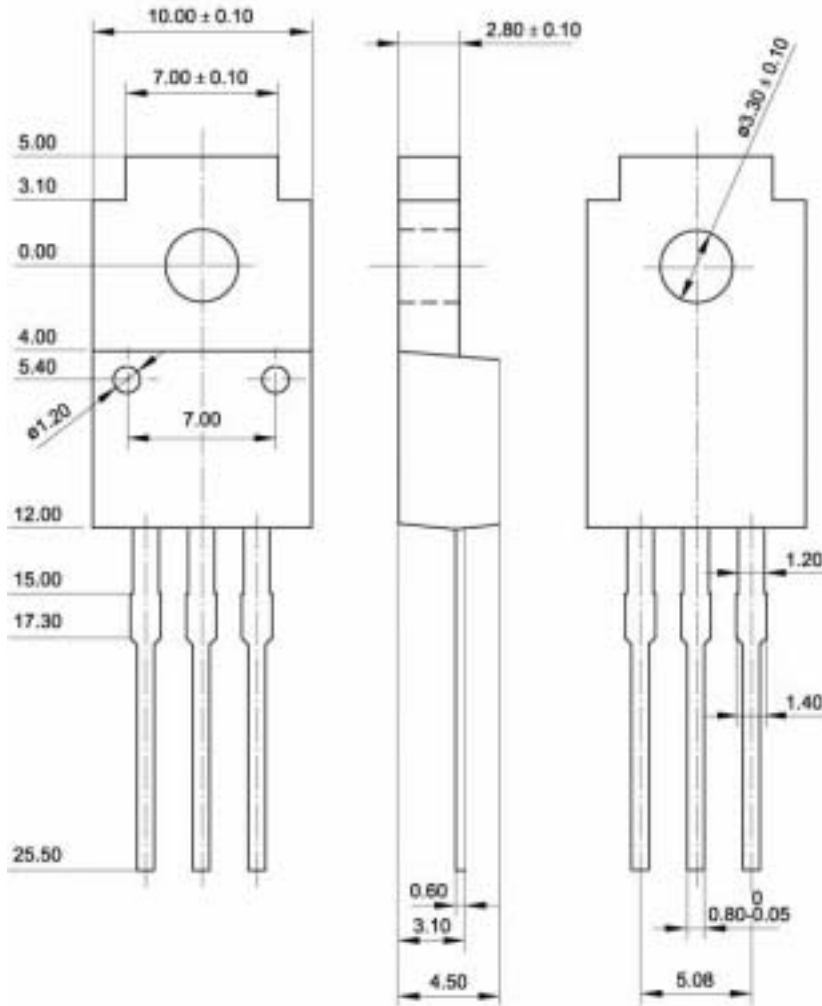


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.15$  mm)

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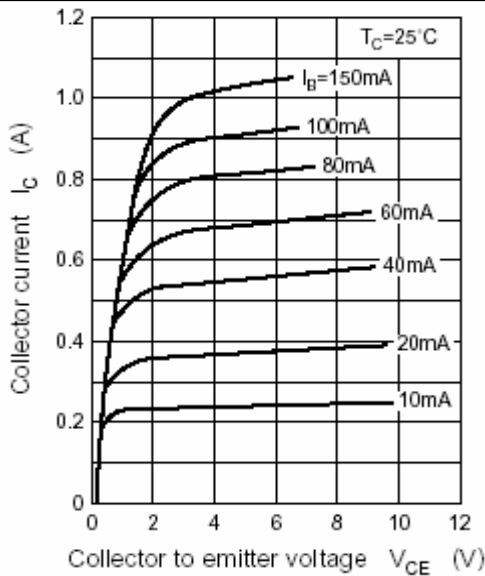


Fig.3 Static Characteristic

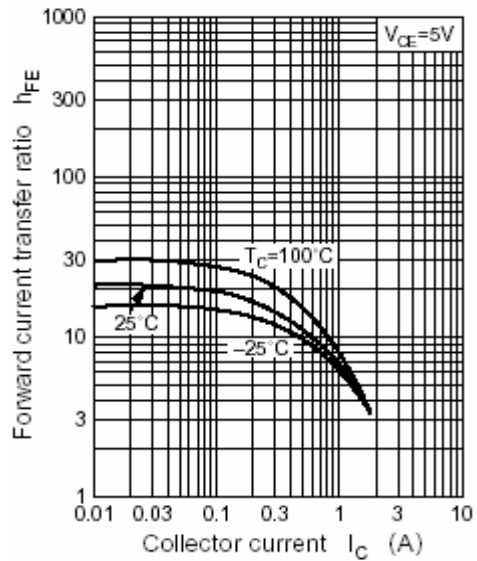


Fig.4 DC current Gain

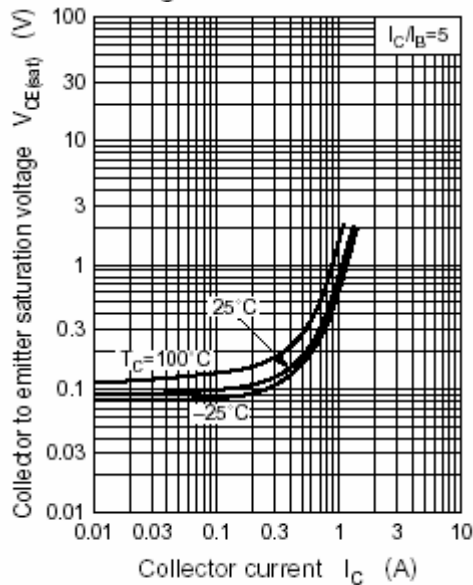


Fig.5 Collector-Emitter Saturation Voltage

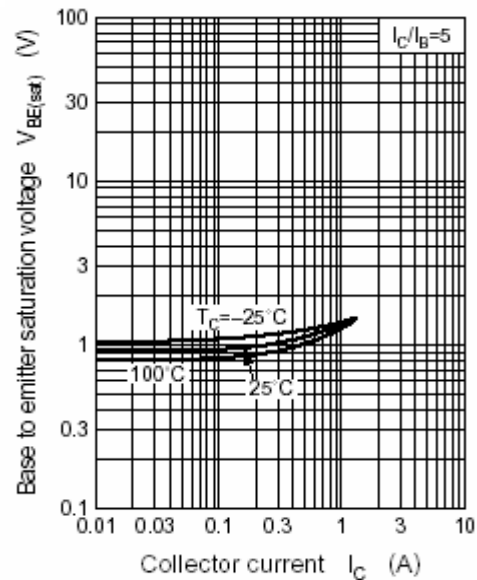


Fig.6 Base-Emitter Saturation Voltage

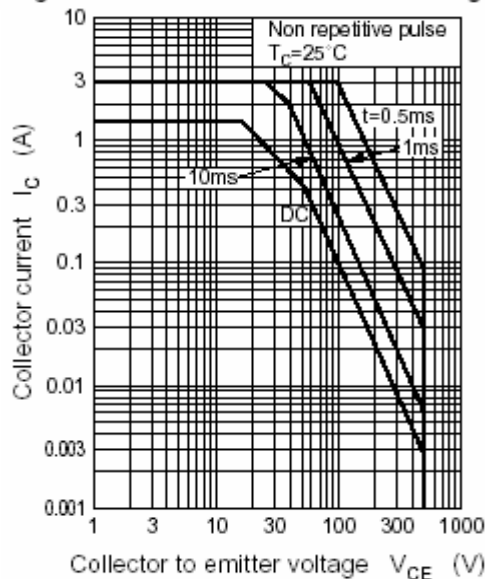


Fig.7 Safe Operating Area